

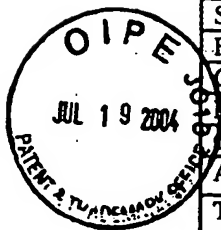
First Named Inventor	Leonard Forbes	INFORMATION DISCLOSURE STATEMENT FORM PTO-1449
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Group Art Unit	2655	
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Confirmation No.	9726	
Attorney Docket No.	400.270US01	
Title: NROM FLASH MEMORY CELL WITH INTEGRATED DRAM		Sheet 1 of 7

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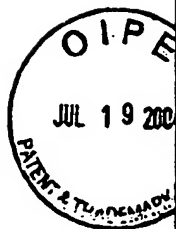
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